



PATENT
005702-20035 (81788/0020)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re application of:

Shota KITAMURA et al.

Serial No: 09/392,865

Filed: September 9, 1999

For: NON-VOLATILE SEMICONDUCTOR
MEMORY DEVICE AND ITS
MANUFACTURING METHOD

Art Unit: 2811

Examiner: Thien F. Tran

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AMENDMENT

Box RCE

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In connection with the continued examination of the above-identified
application pursuant to the Request For Continued Examination (RCE), and
responsive to the final Office Action of March 15, 2002, please amend the application
as follows:

IN THE CLAIMS:

Cancel claims 5-7, 16 and 17, without prejudice.

Please add the following new claims:

-- 18. (NEW) A nonvolatile semiconductor memory device comprising:

a semiconductor substrate;

shallow trench isolation layers which are strip shaped, extending in one
direction, and embedded in a surface of said semiconductor substrate with
predetermined intervals, a strip-shaped memory region being formed between two
adjacent shallow trench isolation layers, and two adjacent memory regions being
isolated by one of said shallow trench isolation layers;